

2812

Docket No. 239525US2/shb



## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Yukio TANIGUCHI, et al.

SERIAL NO: 10/603,771

GAU: 2812

FILED: June 26, 2003

EXAMINER:

FOR: CRYSTALLIZATION APPARATUS, OPTICAL MEMBER FOR USE IN CRYSTALLIZATION APPARATUS, CRYSTALLIZATION METHOD, THIN FILM TRANSISTOR, AND DISPLAY

## INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

## REFERENCES

The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.

A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

## RELATED CASES

Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.

A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

## CERTIFICATION

Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.

No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

## DEPOSIT ACCOUNT

Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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MAIER & NEUSTADT, P.C.

Marvin J. Spivak

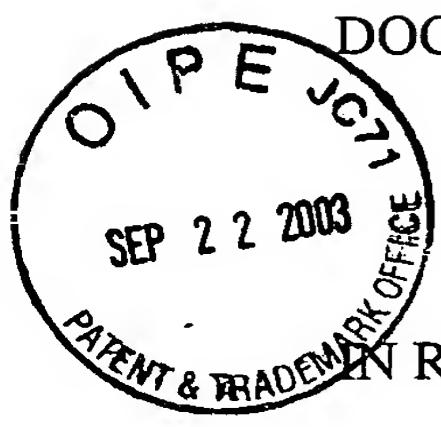
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**STATEMENT OF RELEVANCY**

**Reference AZ on Form 1449:**

Fig. 4 illustrates a phenomenon wherein a laser beam undergoes phase modulation at the shifting portion of a phase shift mask, thereby inclining the wavefront.



Form PTO 1449 (Modified) LIST OF REFERENCES CITED BY APPLICANT		ATTY DOCKET NO. 239525US2		SERIAL NO. 10/603,771	
		APPLICANT Yukio TANIGUCHI, et al.			
		FILING DATE June 26, 2003		GROUP 2812	
		<b>U.S. PATENT DOCUMENTS</b>			
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS SUB CLASS
	AA				
	AB				
	AC				
	AD				
	AE				
	AF				
	AG				
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	AI				
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	AK				
	AL				
	AM				
	AN				
<b>FOREIGN PATENT DOCUMENTS</b>					
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES      NO
	AO				
	AP				
	AQ				
	AR				
	AS				
	AT				
	AU				
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)</b>					
	AV	W. YEH, et al., Jpn. J. Appl. Phys., vol. 41, part 1, no. 4A, pages 1909-1914, "PROPOSED SAMPLE STRUCTURE FOR MARKED ENLARGEMENT OF EXCIMER-LASER-INDUCED LATERAL GRAIN GROWTH IN Si THIN FILMS", April 2002			
	AW	M. NAKATA, et al., Jpn. J. Appl. Phys., vol. 40, part 1, no. 5A, pages 3049-3054, "A NEW NUCLEATION-SIT-CONTROL EXCIMER-LASER-CRYSTALLIZATION METHOD", May 2001			
	AX	C.- H. OH, et al., Jpn. J. Appl. Phys., vol. 37, part 2, no. 5A, pages L492-L495, "A NOVEL PHASE-MODULATED EXCIMER-LASER CRYSTALLIZATION METHOD OF SILICON THIN FILMS", May 1998			
	AY	M. MATSUMURA, et al., Thin Solid Films 337, pages 123-128, "ADVNCED EXCIMER-LASER ANNEALING PROCESS FOR QUASI SINGLE-CRYSTAL SILICON THIN-FILM DEVICES", 1999			
	AZ	M. MATSUMURA, Applied Physics, vol. 71, no. 5, pages 543-547, "EXCIMER-LASER-GROWN SILICON THIN FILMS WITH ULTRALARGE GRAINS", 2002		<input type="checkbox"/> Additional References sheet(s) attached	
Examiner				Date Considered	
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.					